Ordering number:EN1332A

NPN Planar Type Silicon Darlington Transistor

2SC3292

For General-Purpose Drivers

Applications

· Especially suited for use in switching of L load motor driver, printer hammer driver, relay driver, etc.

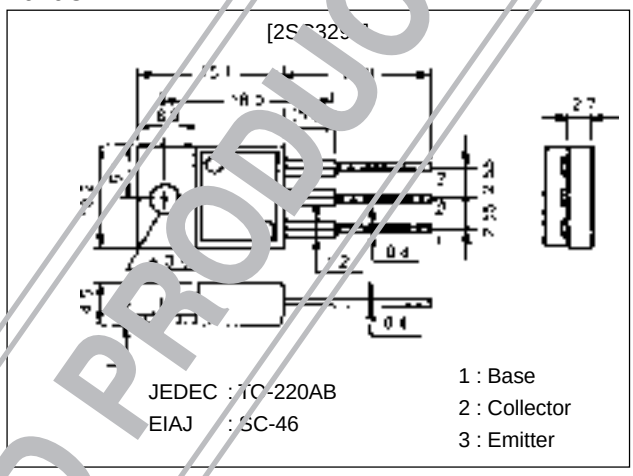
Features

· High DC current gain.
· Large current capacity and wide ASO.
· Contains 60±10V Zener diode between collector and base.
· Uniformity in collector-to-base breakdown voltage due to adoption of accurate impurity diffusion process.
· 15mJ reverse energy rating.

Package Dimensions

unit:mm

2010C



Specifications

Absolute Maximum Ratings at Ta = 25˚C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V_{CBO}		50*	V
Collector-to-Emitter Voltage	V_{CEO}		50*	V
Emitter-to-Base Voltage	V_{EBO}		6	V
Collector Current	I_C		1.2	A
Collector Current (Pulse)	I_{CP}		2.5	A
Base Current	I_B		0.25	A
Collector Dissipation	P_C	T_c=25˚C	20	W
Junction Temperature	Tj		150	˚C
Storage Temperature	Tstg		–55 to +150	˚C

* : Built-in Zener diode (60±10V)

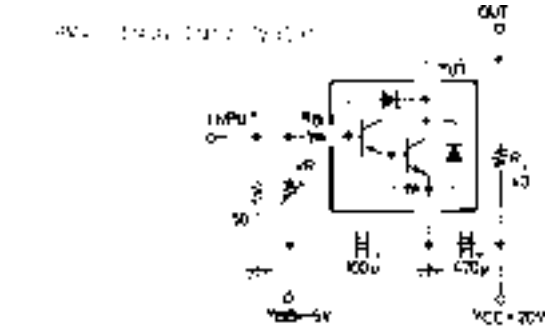
Electrical Characteristics at Ta = 25˚C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	V_{CB}=40V, I_E=0			10	μA
Emitter Cutoff Current	I_{EBO}	V_{EB}=5V, I_C=0			2	mA
DC Current Gain	h_{FE}	V_{CE}=5V, I_C=0.5A	1000	4000		
Gain-Bandwidth Product	f_T	V_{CE}=5V, I_C=0.5A		180		MHz
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=0.5A, I_B=2mA		1.0	1.5	V
Base-to-Emitter Saturation Voltage	$V_{BE(sat)}$	I_C=0.5A, I_B=2mA			2.0	V

SANYO Electric Co.,Ltd. Semiconductor Bussiness Headquaters
TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	I_C=0.1mA, I_E=0	50	60	70	V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=1mA, R_{BE}=∞	50	60	70	V
Unclamped inductive load enaegy	Es/b	L=100mH, R_{BE}=100Ω	15			mJ
Turn-ON Time	t_{on}	V_{CC}=20V, I_C=0.5A, I_{B1}=–I_{B2}=2mA		0.2		μs
Storage Time	t_{stg}	V_{CC}=20V, I_C=0.5A, I_{B1}=–I_{B2}=2mA		2.2		μs
Fall Time	t_f	V_{CC}=20V, I_C=0.5A, I_{B1}=–I_{B2}=2mA		0.4		μs

Switching Time Test Circuit



Unit (resistance: Ω, capacitance: F)

Es/b Test Circuit

Unit (resistance: Ω)